

#### TRD236D

### High voltage fast-switching NPN power transistor

Preliminary data

#### **Features**

- High voltage capability
- Low spread of dynamic parameters
- Minimum lot-to-lot spread for reliable operation
- Very high switching speed
- Integrated antiparallel collector-emitter diode

#### **Applications**

- Electronic ballast for fluorescent lighting
- Electronic transformer for halogen lamps



This device is an NPN power transistor manufactured using high voltage multi epitaxial planar technology for high switching speeds. It uses a cellular emitter structure with planar edge termination to enhance switching speeds while maintaining a satisfactory RBSOA.

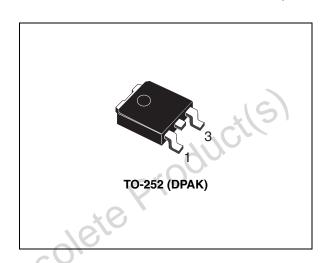


Figure 1. Internal schematic diagram

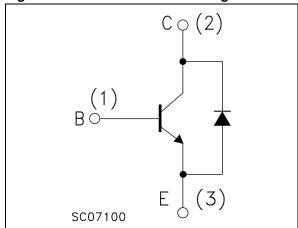


Table 1. Device summary

Part number	Marking	Package	Packaging
TRD236DT4	TRD236D	TO-252	Tape and reel

Contents TRD236D

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TRD236D Electrical ratings

# 1 Electrical ratings

Table 2. Absolute maximum rating

Symbol	Parameter	Value	Unit
$V_{CES}$	Collector-emitter voltage (V <sub>BE</sub> = 0)	700	V
$V_{CEO}$	Collector-emitter voltage (I <sub>B</sub> = 0)	400	V
V <sub>EBO</sub>	Emitter-base voltage $(I_C = 0, I_B = 2 \text{ A}, t_p < 10 \mu\text{s})$	V <sub>(BR)EBO</sub>	V
I <sub>C</sub>	Collector current (I <sub>C</sub> = 0)	4 (C	Α
I <sub>CM</sub>	Collector peak current (t <sub>P</sub> < 5 ms)	8	Α
Ι <sub>Β</sub>	Base current	2	Α
I <sub>BM</sub>	Base peak current (t <sub>P</sub> < 5 ms)	Q4	Α
P <sub>tot</sub>	Total dissipation at $T_c \le 25$ °C	35	W
T <sub>stg</sub>	Storage temperature	-65 to 150	°C
$T_J$	Max. operating junction temperature	150	°C
0	roduci(s)		

**Electrical characteristics** TRD236D

#### **Electrical characteristics** 2

 $(T_{case} = 25 \, ^{\circ}C \text{ unless otherwise specified})$ 

**Electrical characteristics** Table 3.

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I <sub>CES</sub>	Collector cut-off current (V <sub>BE</sub> = 0)	V <sub>CE</sub> = 700 V V <sub>CE</sub> = 700 V T <sub>C</sub> = 125 °C			0.1 0.5	mA mA
I <sub>CEO</sub>	Collector cut-off current (I <sub>B</sub> = 0)	V <sub>CE</sub> = 400 V			0.25	mA
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage (I <sub>C</sub> = 0)	I <sub>E</sub> = 10 mA	9	(	18	٧
V <sub>CEO(sus)</sub> <sup>(1)</sup>	Collector-emitter sustaining voltage (I <sub>B</sub> = 0)	I <sub>C</sub> = 10 mA	400	90		٧
V <sub>CE(sat)</sub> (1)	Collector-emitter saturation voltage	$I_C = 0.8 \text{ A}$ $I_B = 0.1 \text{ A}$ $I_C = 2.5 \text{ A}$ $I_B = 0.6 \text{ A}$			1.1 1.3	V V
V <sub>BE(sat)</sub> (1)	Base-emitter saturation voltage	$I_C = 1 A$ $I_B = 0.2 A$ $I_C = 2.5 A$ $I_B = 0.5 A$			1.2 1.3	V V
h <sub>FE</sub>	DC current gain	$I_C = 10 \text{ mA}$ $V_{CE} = 5 \text{ V}$ $I_C = 2.5 \text{ A}$ $V_{CE} = 5 \text{ V}$	10 8		28	
t <sub>s</sub>	Inductive load Storage time Fall time	$V_{CC} = 200 \text{ V } I_{C} = 2 \text{ A}$ $I_{B1} = 0.4 \text{ A}$ $V_{BE(off)} = -5 \text{ V}$ $R_{BB} = 0 \Omega$ $L = 200 \mu H$ (see Figure 13)		0.6 0.1		μs μs
V <sub>F</sub>	Diode forward voltage	I <sub>F</sub> = 2 A			2.5	V
Pulsed dura	Lation = 300 ms, duty cycle ≤ 1.4	I 5%	I			

### 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

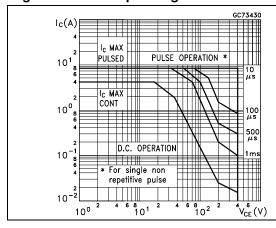


Figure 3. Derating curve

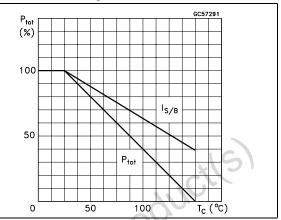


Figure 4. DC current gain (V<sub>CE</sub> = 1.5 V)

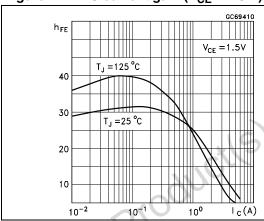


Figure 5. DC current gain  $(V_{CE} = 5 V)$ 

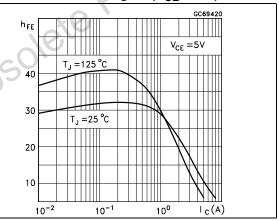
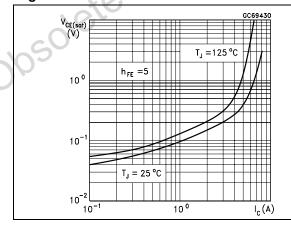
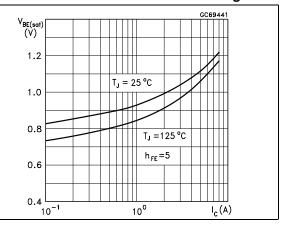


Figure 6. Collector-emitter saturation voltage Figure 7. Base-emitter saturation voltage

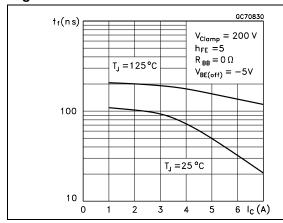




Electrical characteristics TRD236D

Figure 8. Inductive load fall time

Figure 9. Inductive load storage time



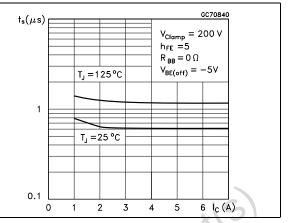
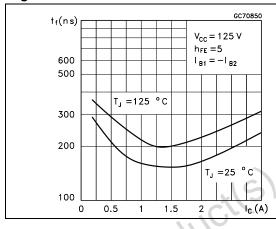


Figure 10. Resistive load fall time

Figure 11. Resistive load storage time



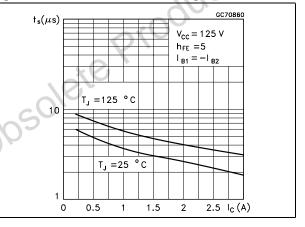
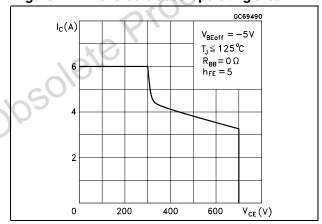
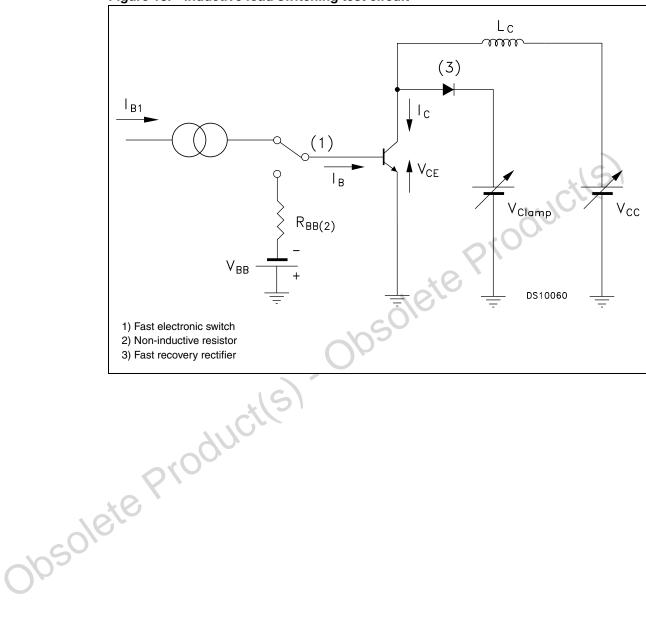


Figure 12. Reverse biased operating area



### 2.2 Test circuits

Figure 13. Inductive load switching test circuit



## 3 Package mechanical data

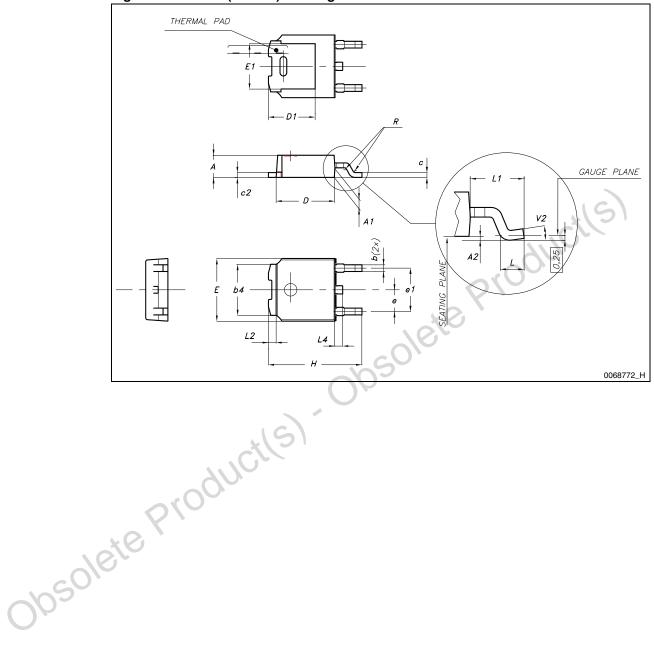
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Table 4. DPAK (TO-252) mechanical data

Dim.	mm			
Dim.	Min.	Тур.	Max.	
Α	2.20		2.40	
A1	0.90		1.10	
A2	0.03		0.23	
b	0.64		0.90	
b4	5.20		5.40	
С	0.45		0.60	
c2	0.48		0.60	
D	6.00		6.20	
D1		5.10	000	
E	6.40	0	6.60	
E1		4.70		
е		2.28		
e1	4.40	60,	4.60	
Н	9.35	103	10.10	
L	1		1.50	
L1	16	2.80		
L2		0.80		
L4	0.60		1	
R	0,	0.20		
V2	0°		8°	

Figure 14. DPAK (TO-252) drawing



TRD236D Revision history

## 4 Revision history

Table 5. Document revision history

Date	Revision	Changes
28-Jun-2011	1	First release



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